

# ELI-NP Young Scientist and Young Engineer Days

• January 10<sup>th</sup>-12<sup>th</sup>, 2022 •

*ELI-NP (IFIN-HH), Măgurele*

TITLE:

**NANOMETER THIN DIAMOND-LIKE CARBON FILMS  
OPTIMIZED FOR LASER TARGETS FOR ELI-NP**

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• *PhD stud. (UPB/SDIALA)* •

## OTHER TEAM MEMBERS

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INFLPR: *PhD Bogdana Mitu, PhD Veronica Sătulu, PhD Valentina Mărăscu*

## LABORATORY SUPPORT

• *Target Laboratory from ELI-NP* •

• *Plasma Processes, Materials and Surfaces Group from INFLPR* •

- Motivation for laser-driven acceleration of carbon ions and protons using targets which consist in free-standing carbonic thin film
- Requirements for free-standing carbonic thin films for this application
- Suitability of diamond-like carbon
- Optimization of growth of diamond-like carbon thin films with required properties
- Characterization methods applied to check compatibility of grown films for free-standing target application
- Conclusions

## MOTIVATION

### Applications of irradiation with ACCELERATED C/H ions:

- testing of materials to ionizing radiation conditions.
- radiotherapy
  - due to high Linear Energy Transfer (LET) of high-energy ions/protons leading to high LET-dependent Relative Radiobiological Effectiveness (RBE). [1] [2]
- diagnostics and imagery. [3] [4] [5] [6]
- isotopes composition changing.
- generating of fluxes of neutrons and nuclei from secondary targets, subsequently usable.

**LASER-DRIVEN ACCELERATION of C/H ions**  
**from carbonic solid film targets**  
(H from film impurities / residual composition)

II  
V

**Fluxes of accelerated C/H ions**  
**much higher than classical accelerators**

- [1] G. Milluzzo & D. Doria, et al., 'Dosimetry of laser-accelerated carbon ions for cell irradiation at ultra-high dose rate', Journal of Physics: Conference Series, vol. 1596, p. 012038, July 2020.
- [2] D. Schardt, 'Tumor therapy with high-energy carbon ion beams', Nuclear Physics A 787 (2007) 633c–641c.
- [3] M. Barberio, et al., 'Laser-Accelerated Proton Beams as Diagnostics for Cultural Heritage', Scientific Reports, 7:40415 (2017).
- [4] H.-J. Ziock, et al., 'The proton radiography concept', LA-UR-98-1368, <http://lib-www.lanl.gov/la-pubs/00460235.pdf>.
- [5] G. Poludniowski, et al., 'Proton radiography and tomography with application to proton therapy', BJR 2015, 88:105320150134.
- [6] Lina Sheng, et al., 'Heavy-ion radiography facility at the Institute of Modern Physics', Laser and Particle Beams (2014), 32, 651-655.

# MOTIVATION

Fluxes of C/H ions  
**without other** elements  
than C and H

II  
V

Carbonic solid film **target**  
**without other** elements  
than C and H

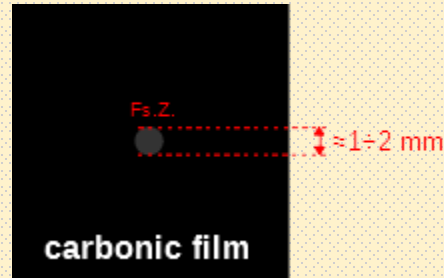
II  
V

**Target** consisting  
by carbonic solid **film**  
with **free-standing** pattern  
on **substrate**  
with **holes** pattern

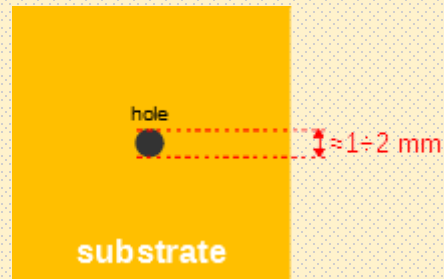
<=

Carbonic solid **film**  
will be **grown on substrate**

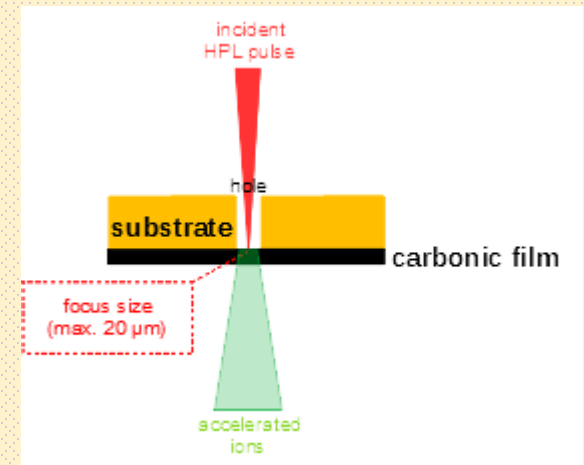
*Target rear view*  
(Fs.Z. is free-standing zone)



*Target front view*



*Target lateral view*  
during laser-film interaction



## REQUIREMENTS

### THICKNESS of carbonic target:

- From **nanometers** to **micrometers** to accelerate **C** and/or **H** ions by **two main mechanisms** or **combination of these**:
    - **RPA (ultrathin/thin films)** which allows **highest kinetic energies** of **laser-driven** acceleration technique;
    - **TNSA (thin/thick films)** which has **less requirements** than **RPA** about **laser pulse** (duration, contrast, intensity), **advantageous** in applications which **don't need high kinetic energies**.
- [7] [8] [9] [10] [11] [12]

### ROUGHNESS of carbonic target:

- **Bellow of  $\lambda/10$**  on surface zones which have sizes **higher** than laser spot diffraction limit  **$1.2\lambda$**

$$\lambda=820 \text{ nm for ELI-NP HPL pulses} \Rightarrow \left\{ \begin{array}{l} \lambda/10=82 \text{ nm} \\ 1.2\lambda=984 \text{ nm} \end{array} \right.$$

### MECHANICAL STRENGTH of carbonic target:

- **High resistance** to mechanical tensile to avoid breaking by **target manipulation**, because of **high ratio aspect of free-standing zones**.

[7] D. Sangwan & D. Stutman & B. Diaconescu, et al., 'Simulations of carbon ion acceleration by 10 PW laser pulses on ELI-NP', Laser and Particle Beams, volume 37, issue 4, 2019, pp. 346-353.

[8] C. Scullion, D. Doria, et al., 'Polarization Dependence of Bulk Ion Acceleration from Ultrathin Foils Irradiated by High-Intensity Ultrashort Laser Pulses', Phys. Rev. Lett., vol. 119, no. 5, p. 054801, 2017.

[9] Bulanov S. S., et al., 'Optimized laser pulse profile for efficient radiation pressure acceleration of ions', Physics of Plasmas 19 (2012) 093112.

[10] D. Jung, et al., 'Laser-driven 1 GeV carbon ions from preheated diamond targets in the break-out afterburner regime', Physics of Plasmas, vol. 20, p. 083103, 2013.

[11] B. M. Hegelich, et al., 'Laser-driven ion acceleration from relativistically transparent nanotargets', New Journal of Physics, vol. 15, p. 085015, 2013.

[12] D. Jung, et al., 'Efficient carbon ion beam generation from laser-driven volume acceleration', New Journal of Physics, vol. 15, p. 023007, 2013.

## DIAMOND-LIKE CARBON (DLC)

**Suitable carbonic materials** for such target films to C/H ions acceleration:

- Crystalline structures:

**sp<sup>2</sup>** hybridized C

- **graphene: film** having **only ultrathin** thicknesses => **suitable only** for **some** acceleration mechanisms  
(if target doesn't contain a film from below carbonic materials, supplementary to graphene film)

**sp<sup>3</sup>** hybridized C:

- **diamond: film** growth **requires very high** temperature/pressure for **one step** fabrication<sup>\*)</sup>

- Amorphous structures:

**sp<sup>3</sup>** and **sp<sup>2</sup>** hybridized C:

- **DLC: film** growth **can be** performed at **room/low** temperature in **vacuum** conditions for **one step** fabrication,<sup>\*)</sup>  
e.g. radio-frequency plasma-enhanced chemical vapor deposition (RF-PECVD)

**\*) one step fabrication = synthesis and film deposition in same time**

**DLC:**

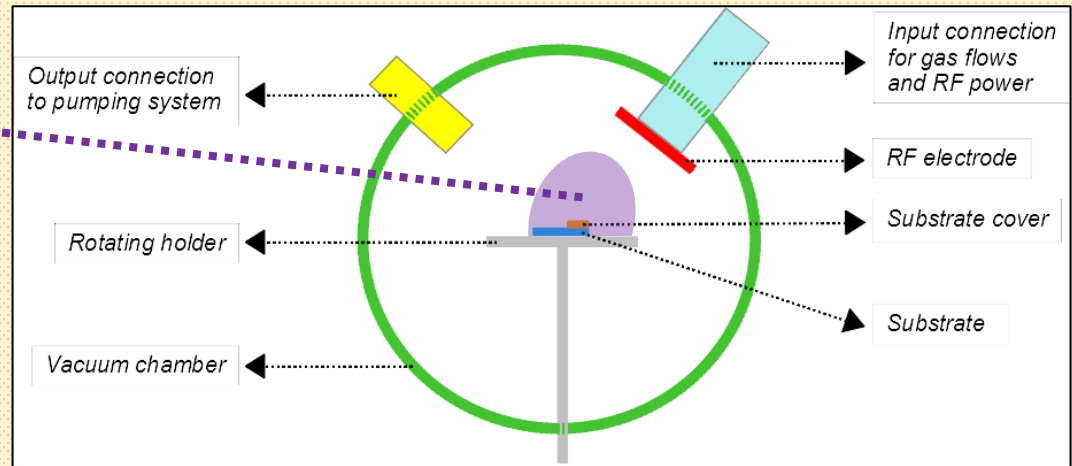
- **DLC** contains **sp<sup>3</sup>** hybridized C in diamond (**cubic diamond**) and lonsdaleite (**hexagonal diamond**)  
**local** crystalline structures **without to form clearly separated crystallites** => **DLC is amorphous**
- **real DLC** contains **sp<sup>2</sup>** hybridized C (*in graphite form*), **in addition** to **sp<sup>3</sup>** C, because of **inherent imperfections** of **growth processes** => **mechanical** characteristics of **DLC** are **worsened** if **graphite content** is too high,  
**relative to requirements** of **DLC specific application** => **growth process optimization** to **reduce sp<sup>2</sup> C content**

## DLC GROWTH

### RF plasma ions:

$[\text{CH}_3]^{n+}$ ,  $[\text{CH}_2]^{n+}$ ,  $[\text{CH}]^{n+}$ ,  $[\text{C}]^{n+}$ ,  
 $[\text{H}_2]^+$ ,  $[\text{H}]^+$ ,  $[\text{Ar}]^{n+}$

- Carbon from plasma constituents is deposited, forming  $\text{sp}^3$  &  $\text{sp}^2$  carbonic structures in film.
  - Hydrogen more preferentially etches  $\text{sp}^3$  than  $\text{sp}^2$  carbon, from film.
  - Globally,  $\text{sp}^3$  structures are favored to grow
  - More hydrogen content in plasma leads to more  $\text{sp}^3$  C concentration in film (better DLC).
- [13]



DLC growth experimental set-up (RF-PECVD)

substrate cover => portion of substrate uncoated by DLC => determination of DLC film thickness

## DLC GROWTH

Clean silicon wafers as substrates =>

=> Very smooth substrates =>

=> Worsening of DLC film roughnesses by substrates roughnesses is excluded =>

=> IF such worsening occurs, find of cause will focus on deposition process

### METHOD 1

Precursor gas mixture	$\underline{C}H_4 + Ar$	Total pressure	$\sim 10^{-3} \text{ mbar}$
C:H ratio	1:4	RF power	100 W
Gas flows	25 sccm $CH_4$ 50 sccm Ar	Deposition times	200 min ; 300 min

### METHOD 2

Precursor gas mixture	$\underline{C}H_4 + H_2$	Total pressure	$\sim 1.5 \times 10^{-3} \text{ mbar}$
C:H ratio	1:9 (increased H content)	RF power	100 W
Gas flows	25.0 sccm $CH_4$ 62.5 sccm $H_2$	Deposition times	23 min ; 34 min ; 45 min ; 60 min



# DLC GROWTH

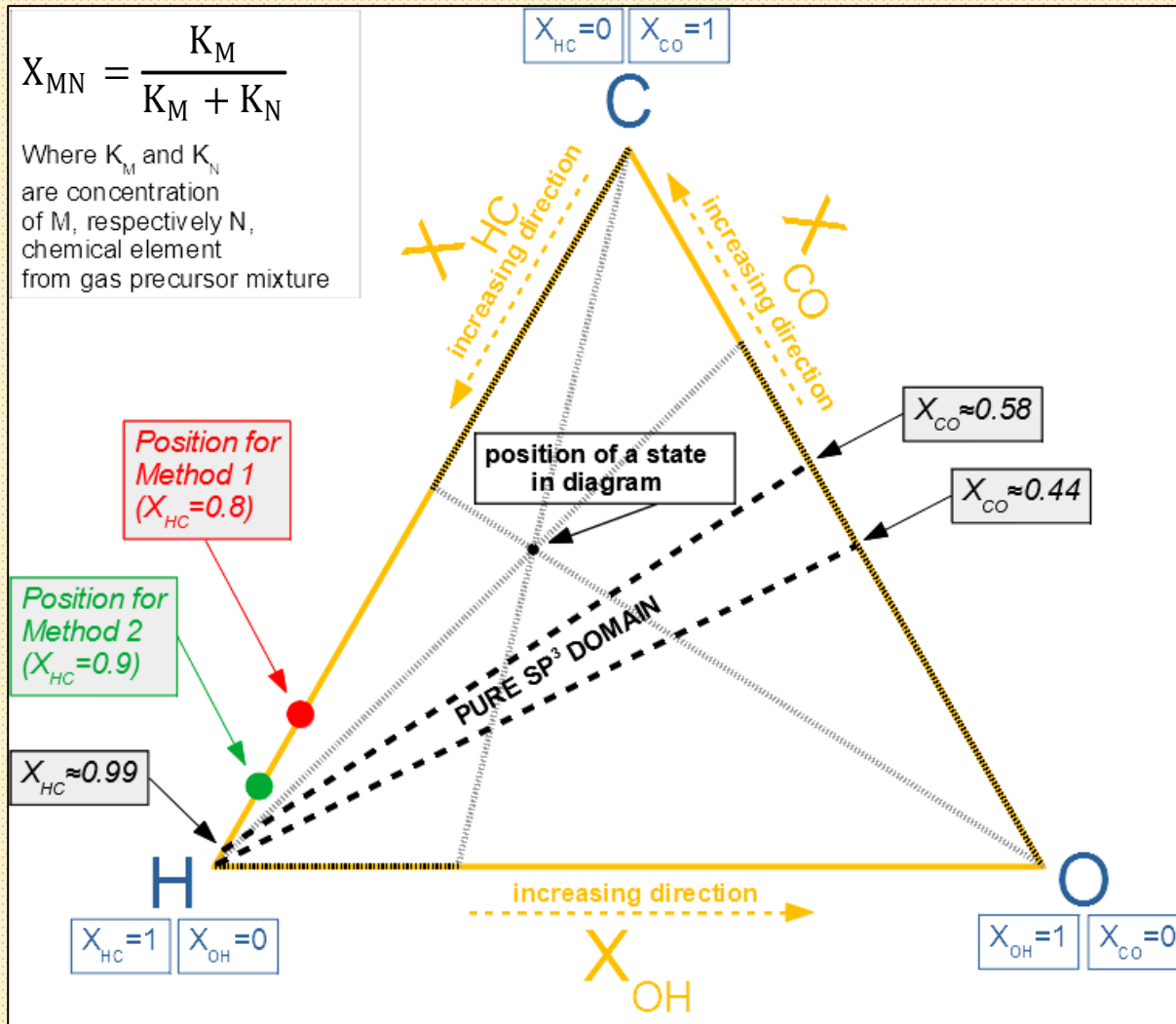
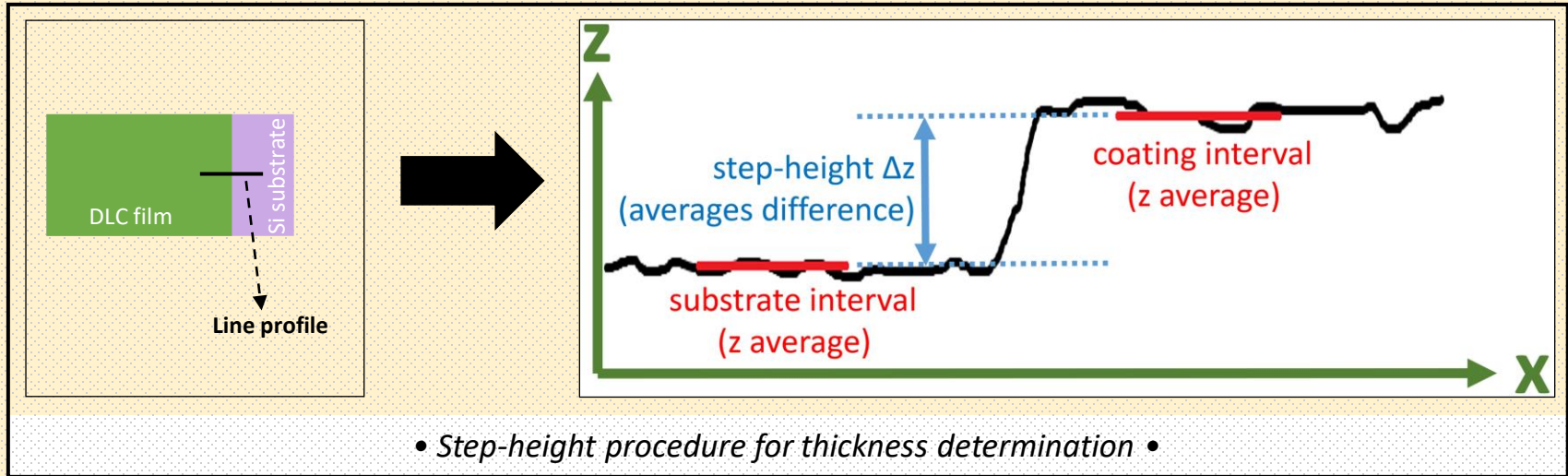


Diagram of pure  $sp^3$  deposited carbonic films, related to C/H/O-composition of precursor gas mixture, for CVD processes [13]

# DLC CHARACTERIZATION

## CONTACT (MECHANICAL) PROFILOMETRY



### METHOD 1 SAMPLES

Deposition time $\Delta t$ [min]	200	300
Thickness $\Delta z$ [nm]	381.7	535.5

$\Delta z(\Delta t)$   
linear fit

Deposition rate  
(slope)

1.8 nm/min

### METHOD 2 SAMPLES

Deposition time [min]	23	34	45	60
Thickness [nm]	21.8	26.3	50.6	57.0

$\Delta z(\Delta t)$   
linear fit

Deposition rate  
(slope)

1.0 nm/min

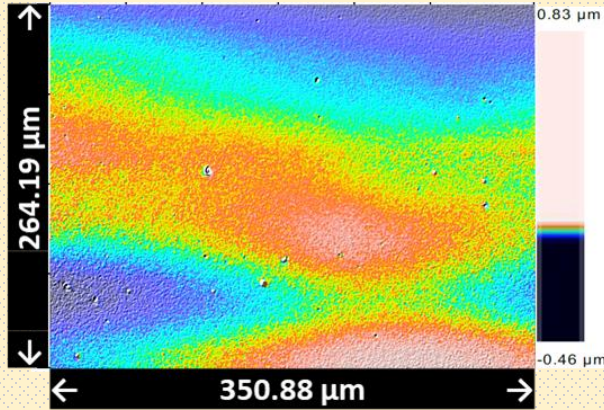
# DLC CHARACTERIZATION

## METHOD 1 samples

200 min  
deposition  
time

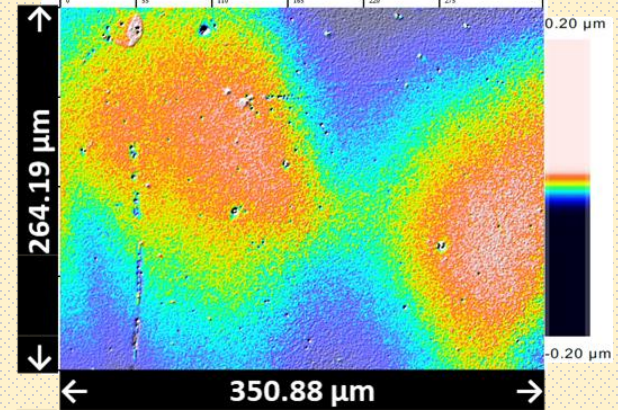
roughness  
 $S_q=18.6\text{nm}$

HPL focus spot  
diffraction limit:  
 $1.2\lambda=0.98\text{ }\mu\text{m}$



300 min  
deposition  
time

roughness  
 $S_q=14.8\text{nm}$



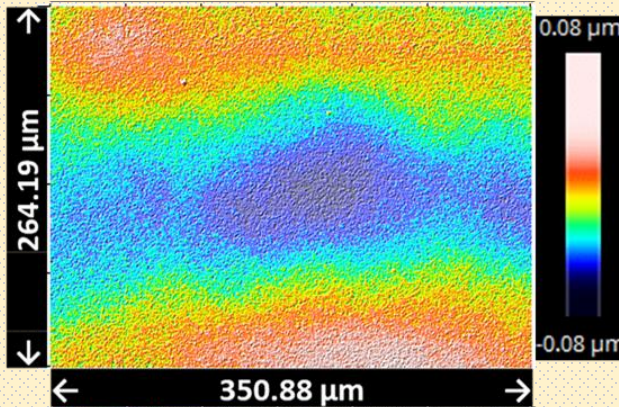
**OPTICAL PROFILOMETRY → Roughness determination → Placement under of  $\lambda/10=82\text{ nm}$**

## METHOD 2 samples

23 min  
deposition  
time

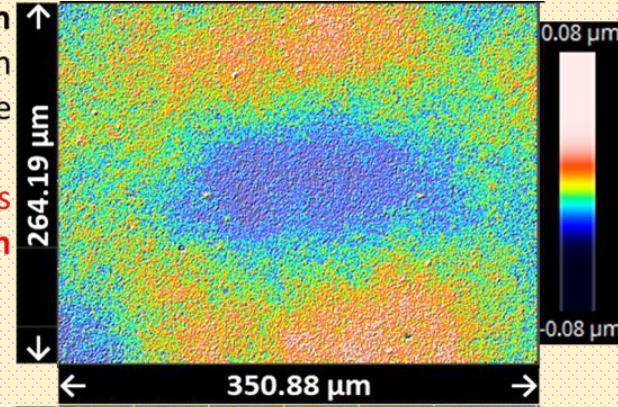
roughness  
 $S_q=2.9\text{ nm}$

HPL focus spot  
diffraction limit:  
 $1.2\lambda=0.98\text{ }\mu\text{m}$



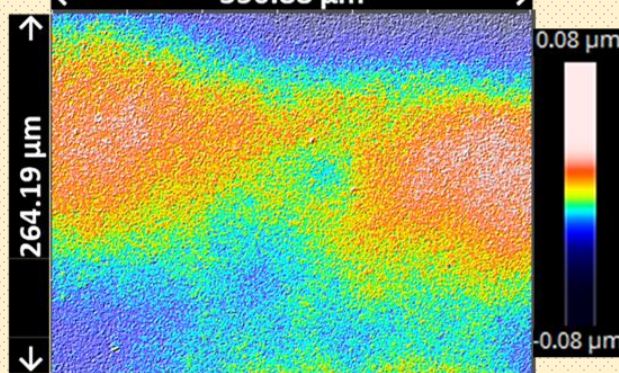
45 min  
deposition  
time

roughness  
 $S_q=1.6\text{ nm}$



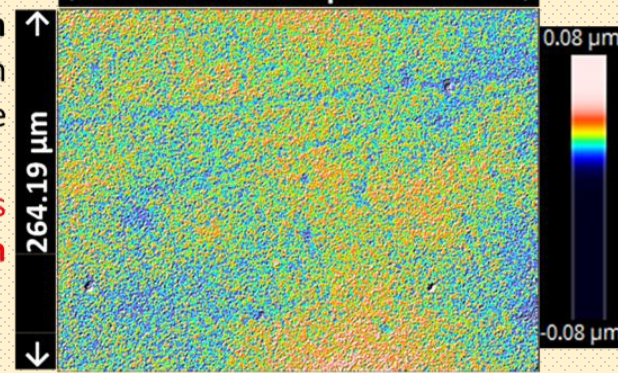
34 min  
deposition  
time

roughness  
 $S_q=2.7\text{ nm}$



60 min  
deposition  
time

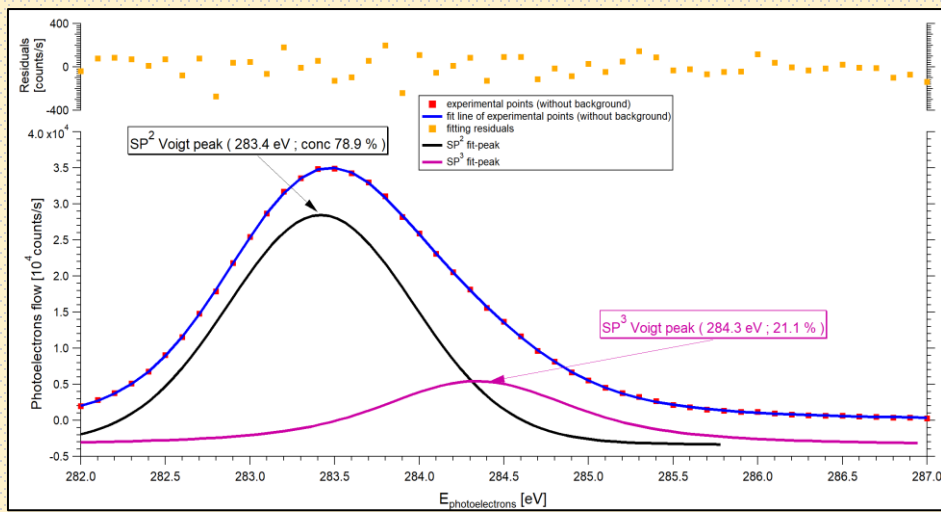
roughness  
 $S_q=1.9\text{ nm}$



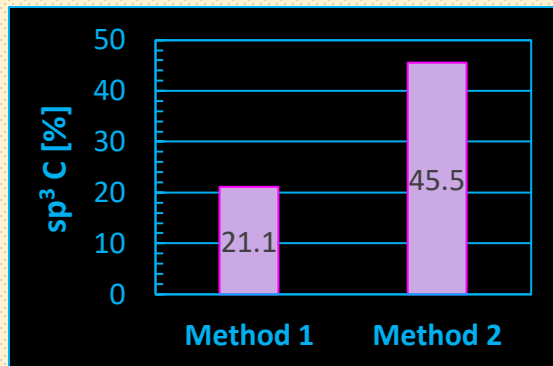
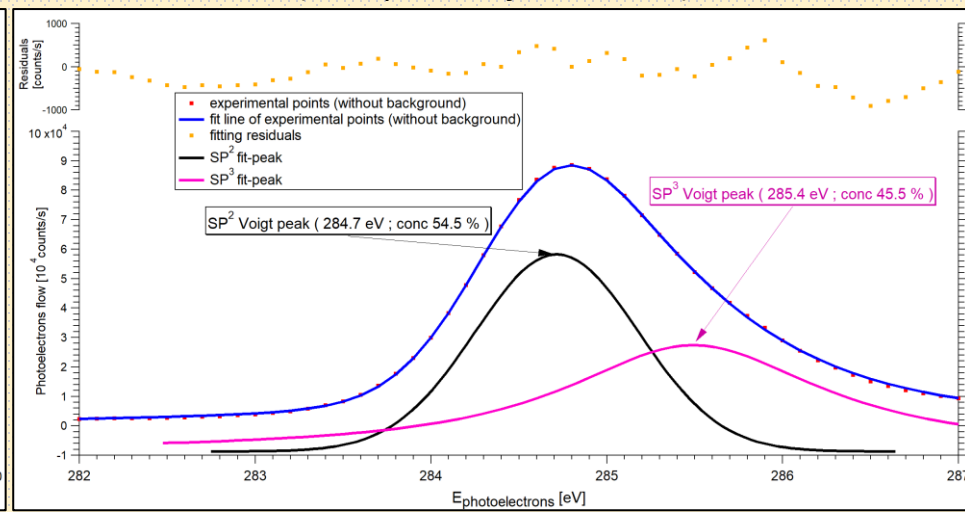
# DLC CHARACTERIZATION

## X-RAY PHOTOEMISSION SPECTROMETRY (XPS)

DLC film from **method 1** deposition  
(XPS spectra of C-C bonds)



DLC film from **method 2** deposition  
(XPS spectra of C-C bonds)



Improving of DLC film **mechanical strength**  
by **method 2**, comparing to **method 1**



## CONCLUSIONS

### CONCLUSION

*Characterization data shows compliance of grown DLC films with HPL target requirements:*

- *$\lambda/10$  limit of roughnesses on large area ( $\approx 92700 \mu\text{m}^2$ )*
- *$sp^3$  C content assures mechanical strength for application concerned*

### NEXT STEPS

- *Implementation of developed growth method on copper substrates (much cheaper than silicon wafers)*
- *Patterned etching of copper substrates to achieve free-standing zones of deposited DLC film*
- *HPL acceleration of carbon & hydrogen ions using DLC targets*

**THANK YOU**  
**FOR ATTENTION**

**!!!**